

# DATA SHEET

**LLE16120X**

**NPN microwave power transistor**

Product specification  
Supersedes data of November 1994

1997 Feb 18

# NPN microwave power transistor

# LLE16120X

### FEATURES

- Diffused emitter ballasting resistors providing excellent current sharing and withstanding a high VSWR
- Interdigitated structure provides high emitter efficiency
- Gold metallization realizes very good stability of the characteristics and excellent lifetime
- Multicell geometry gives good balance of dissipated power and low thermal resistance
- Internal input prematching ensures good stability and allows an easier design of wideband circuits.

### APPLICATIONS

Intended for use in common emitter, class AB power amplifiers in CW conditions for professional applications at 1.65 GHz.

### DESCRIPTION

NPN silicon planar epitaxial microwave power transistor in a SOT437A glued cap metal ceramic flange package, with emitter connected to flange.

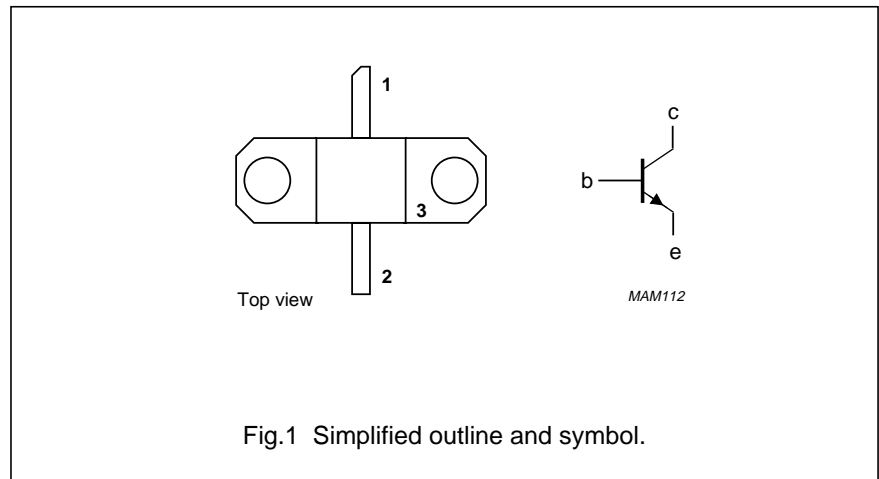
### QUICK REFERENCE DATA

Microwave performance up to  $T_{mb} = 25\text{ }^{\circ}\text{C}$  in a common emitter class AB amplifier.

MODE OF OPERATION	f (GHz)	V <sub>CE</sub> (V)	I <sub>CQ</sub> (A)	P <sub>L1</sub> (W)	G <sub>po</sub> (dB)	Z <sub>i</sub> ; Z <sub>L</sub> (Ω)
Class AB (CW)	1.65	24	0.1	≥11	≥8.7	see Figs 8 and 9

### PINNING - SOT437A

PIN	DESCRIPTION
1	collector
2	base
3	emitter connected to flange



### WARNING

#### Product and environmental safety - toxic materials

This product contains beryllium oxide. The product is entirely safe provided that the BeO disc is not damaged. All persons who handle, use or dispose of this product should be aware of its nature and of the necessary safety precautions. After use, dispose of as chemical or special waste according to the regulations applying at the location of the user. It must never be thrown out with the general or domestic waste.

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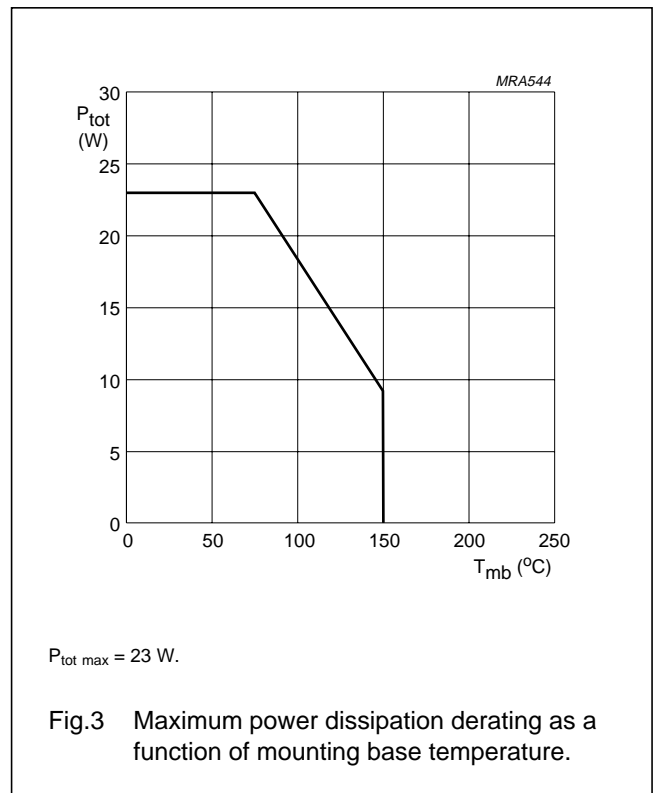
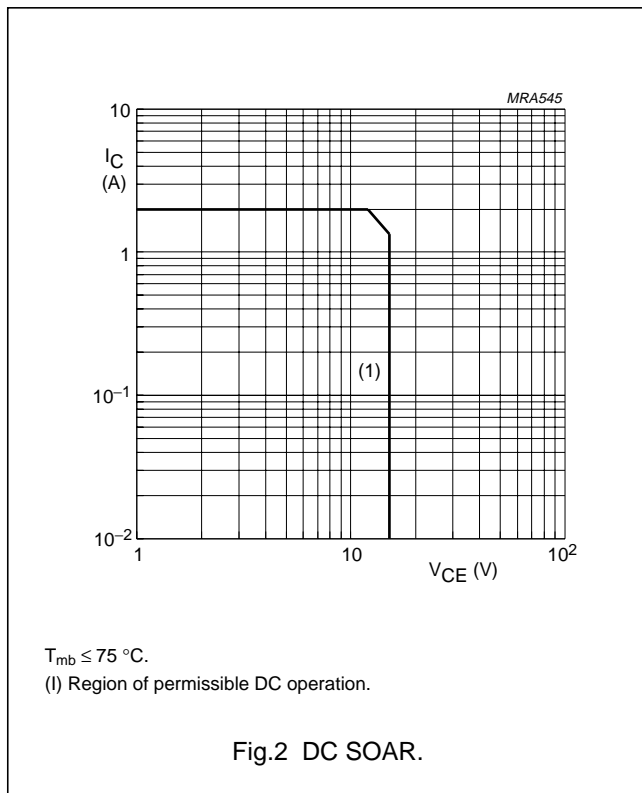
**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter	–	45	V
V <sub>CER</sub>	collector-emitter voltage	R <sub>BE</sub> = 220 Ω	–	30	V
V <sub>CEO</sub>	collector-emitter voltage	open base	–	15	V
V <sub>EBO</sub>	emitter-base voltage	open collector	–	3	V
I <sub>C</sub>	collector current (DC)		–	2	A
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 75 °C	–	23	W
T <sub>stg</sub>	storage temperature		–65	+150	°C
T <sub>j</sub>	junction temperature		–	200	°C
T <sub>slid</sub>	soldering temperature	t ≤ 10 s; note 1	–	235	°C

**Note**

- Up to 0.2 mm from ceramic.



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## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
$R_{th\ j-mb}$	thermal resistance from junction to mounting base	$T_j = 100\text{ °C}$	4.2	K/W
$R_{th\ mb-h}$	thermal resistance from mounting base to heatsink	note1	0.2	K/W

## Note

- See "Mounting recommendations in the General part of handbook SC19a".

## CHARACTERISTICS

$T_j = 25\text{ °C}$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$I_{CBO}$	collector cut-off current	$V_{CB} = 20\text{ V}; I_E = 0$	–	1	mA
$V_{(BR)CER}$	collector-emitter breakdown voltage	$I_C = 5\text{ mA}; R_{BE} = 220\ \Omega$	30	–	V
$V_{(BR)CBO}$	collector-base breakdown voltage	$I_C = 5\text{ mA}; I_B = 0$	45	–	V
$V_{(BR)EBO}$	emitter-base breakdown voltage	$I_E = 5\text{ mA}; I_C = 0$	3	–	V
$h_{FE}$	DC current gain	$V_{CE} = 3\text{ V}; I_C = 1\text{ A}$	15	100	

## APPLICATION INFORMATION

Microwave performance up to  $T_{mb} = 25\text{ °C}$  in a common emitter class AB amplifier (note 1).

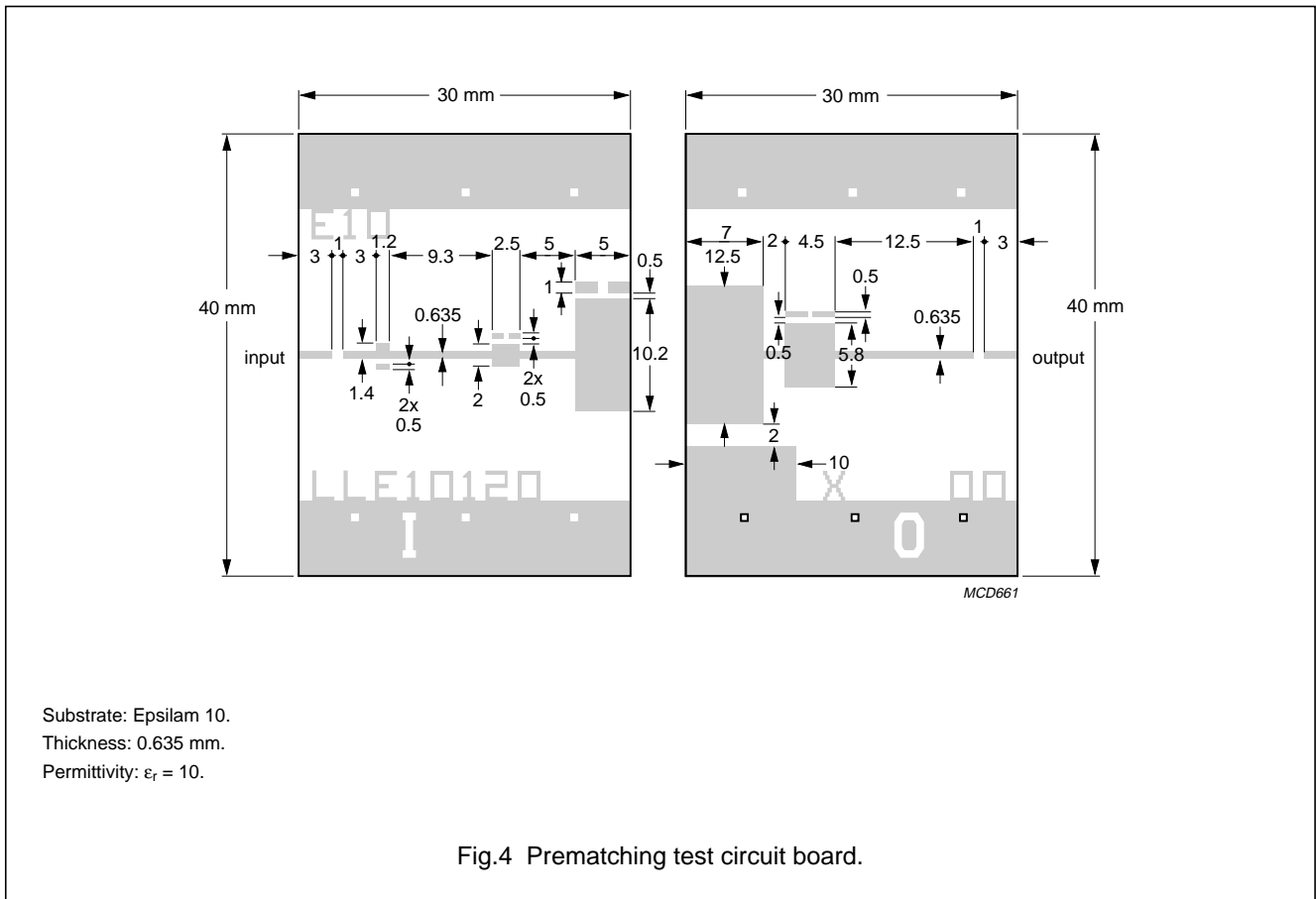
MODE OF OPERATION	f (GHz)	$V_{CE}$ (V)	$I_{CQ}$ (A)	$P_{L1}$ (W)	$G_{po}$ (dB)	$\eta_c$ (%)	$Z_i; Z_L$ ( $\Omega$ )
Class AB (CW)	1.65	24	0.1	$\geq 11$ ; typ. 13	$\geq 8.7$ ; typ. 10.8	typ. 45	see Figs 8 and 9

## Note

- The test circuit is split into 2 independant halves each being  $30 \times 40\text{ mm}$  in size.

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List of components (see bias circuit)

COMPONENT	DESCRIPTION	VALUE	ORDERING INFORMATION
TR1	transistor, BDT85 (or equivalent)		
D1	diode, BY239800 (or equivalent); note 1		
D2	diode, BY239800; note 2		
R1	resistor	100 $\Omega$	
R2	resistor	3.3 k $\Omega$	
R3	resistor	56 $\Omega$	
P1	potentiometer, 10 turns (sfernice)	4.7 k $\Omega$	
C1	electrolytic capacitor	10 $\mu$ F, 40 V	
C5, C6	feedthrough bypass capacitor	1500 pF	Erie, ref. 1250-003
L1	5 turns 0.5 mm copper wire with ferrite bead		
L2	5 turns 0.5 mm copper wire		

Notes

1. In thermal contact with TR1.
2. In thermal contact with D.U.T.

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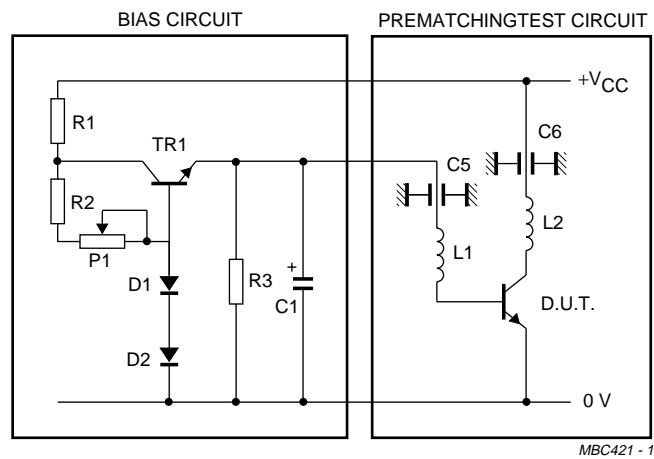
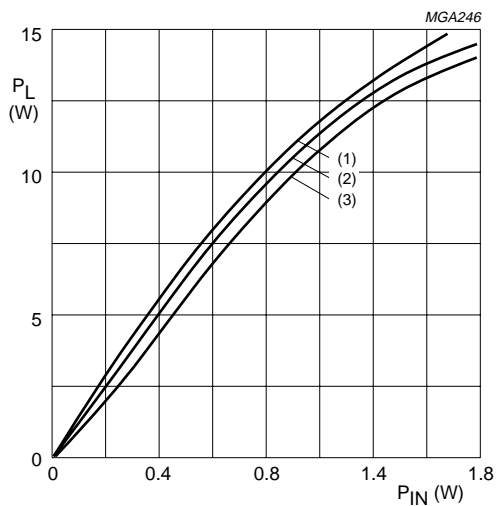
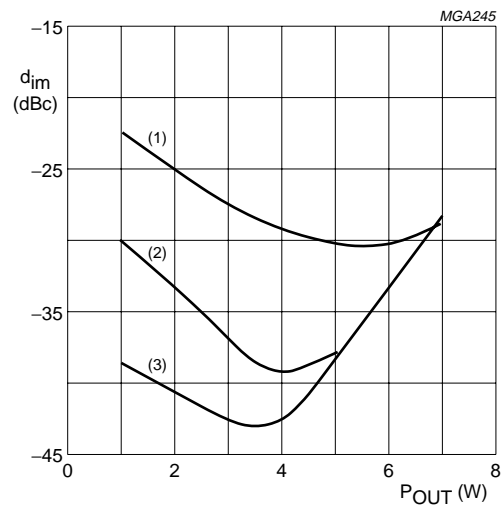


Fig.5 Class AB bias circuit at 1.65 GHz.



$V_{CE} = 24 \text{ V}; f = 1.65 \text{ GHz}.$   
 (1)  $I_{CQ} = 100 \text{ mA}.$   
 (2)  $I_{CQ} = 30 \text{ mA}.$   
 (3)  $I_{CQ} = 3 \text{ mA}.$

Fig.6 Load power as a function of input power.

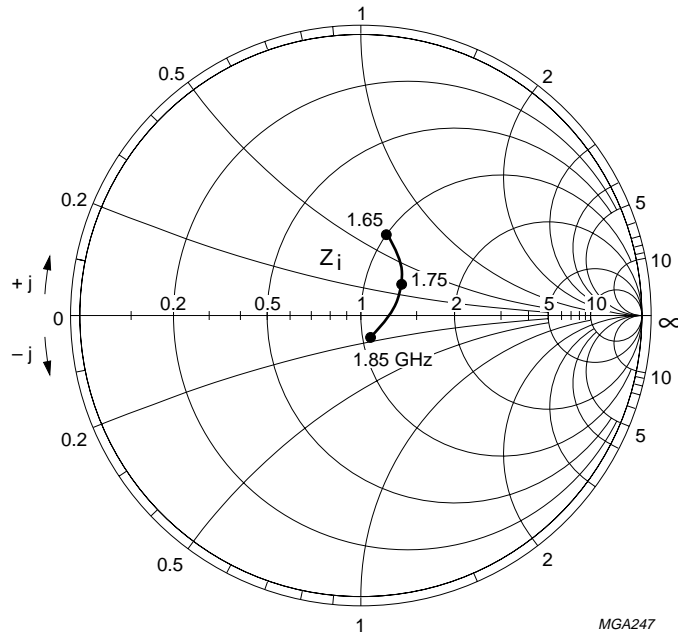


$V_{CE} = 24 \text{ V}; f_1 = 1.65 \text{ GHz}; f_2 = 1.6502 \text{ GHz}.$   
 (1)  $I_{CQ} = 3 \text{ mA}.$   
 (2)  $I_{CQ} = 30 \text{ mA}.$   
 (3)  $I_{CQ} = 100 \text{ mA}.$

Fig.7 Intermodulation distortion as a function of average output power.

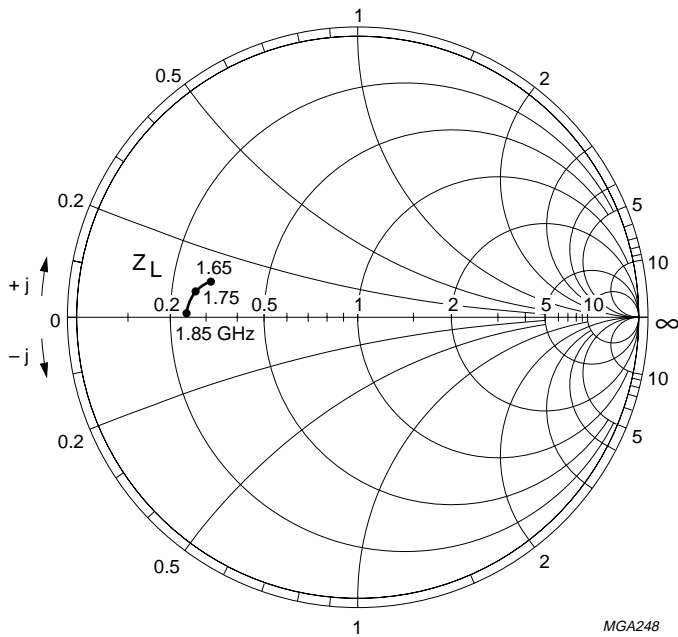
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$V_{CE} = 24 \text{ V}$ ;  $Z_o = 10 \Omega$ ;  $I_{CQ} = 0.1 \text{ A}$ .

Fig.8 Input impedance as a function of frequency; typical values.



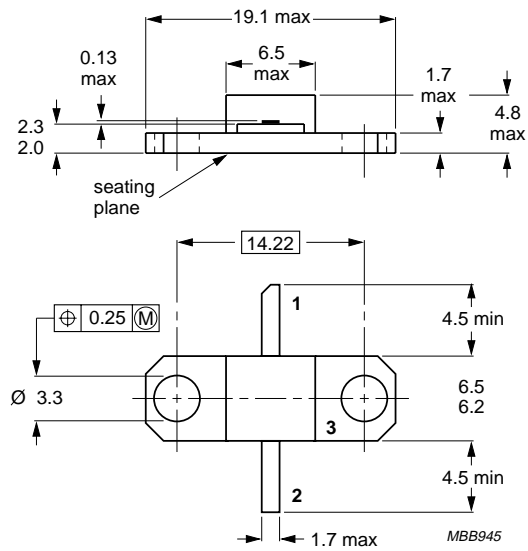
$V_{CE} = 24 \text{ V}$ ;  $Z_o = 10 \Omega$ ;  $I_{CQ} = 0.1 \text{ A}$ .

Fig.9 Optimum load impedance as a function of frequency; typical values.

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PACKAGE OUTLINE



Dimensions in mm.  
 Torque on screws: max. 0.5 Nm.  
 Recommended screw: M3.  
 Recommended pitch for mounting screw: 19 mm.

Fig.10 SOT437A.



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**DEFINITIONS**

<b>Data Sheet Status</b>	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
<b>Limiting values</b>	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
<b>Application information</b>	
Where application information is given, it is advisory and does not form part of the specification.	

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**NOTES**

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# Philips Semiconductors – a worldwide company

**Argentina:** see South America

**Australia:** 34 Waterloo Road, NORTH RYDE, NSW 2113,  
Tel. +61 2 9805 4455, Fax. +61 2 9805 4466

**Austria:** Computerstr. 6, A-1101 WIEN, P.O. Box 213,  
Tel. +43 1 60 101, Fax. +43 1 60 101 1210

**Belarus:** Hotel Minsk Business Center, Bld. 3, r. 1211, Volodarski Str. 6,  
220050 MINSK, Tel. +375 172 200 733, Fax. +375 172 200 773

**Belgium:** see The Netherlands

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**Bulgaria:** Philips Bulgaria Ltd., Energoproject, 15th floor,  
51 James Bourchier Blvd., 1407 SOFIA,  
Tel. +359 2 689 211, Fax. +359 2 689 102

**Canada:** PHILIPS SEMICONDUCTORS/COMPONENTS,  
Tel. +1 800 234 7381

**China/Hong Kong:** 501 Hong Kong Industrial Technology Centre,  
72 Tat Chee Avenue, Kowloon Tong, HONG KONG,  
Tel. +852 2319 7888, Fax. +852 2319 7700

**Colombia:** see South America

**Czech Republic:** see Austria

**Denmark:** Prags Boulevard 80, PB 1919, DK-2300 COPENHAGEN S,  
Tel. +45 32 88 2636, Fax. +45 31 57 1949

**Finland:** Sinikalliontie 3, FIN-02630 ESPOO,  
Tel. +358 9 615800, Fax. +358 9 61580/xxx

**France:** 4 Rue du Port-aux-Vins, BP317, 92156 SURESNES Cedex,  
Tel. +33 1 40 99 6161, Fax. +33 1 40 99 6427

**Germany:** Hammerbrookstraße 69, D-20097 HAMBURG,  
Tel. +49 40 23 53 60, Fax. +49 40 23 536 300

**Greece:** No. 15, 25th March Street, GR 17778 TAVROS/ATHENS,  
Tel. +30 1 4894 339/239, Fax. +30 1 4814 240

**Hungary:** see Austria

**India:** Philips INDIA Ltd, Shivsagar Estate, A Block, Dr. Annie Besant Rd.  
Worli, MUMBAI 400 018, Tel. +91 22 4938 541, Fax. +91 22 4938 722

**Indonesia:** see Singapore

**Ireland:** Newstead, Clonskeagh, DUBLIN 14,  
Tel. +353 1 7640 000, Fax. +353 1 7640 200

**Israel:** RAPAC Electronics, 7 Kehilat Saloniki St, TEL AVIV 61180,  
Tel. +972 3 645 0444, Fax. +972 3 649 1007

**Italy:** PHILIPS SEMICONDUCTORS, Piazza IV Novembre 3,  
20124 MILANO, Tel. +39 2 6752 2531, Fax. +39 2 6752 2557

**Japan:** Philips Bldg 13-37, Kohnan 2-chome, Minato-ku, TOKYO 108,  
Tel. +81 3 3740 5130, Fax. +81 3 3740 5077

**Korea:** Philips House, 260-199 Itaewon-dong, Yongsan-ku, SEOUL,  
Tel. +82 2 709 1412, Fax. +82 2 709 1415

**Malaysia:** No. 76 Jalan Universiti, 46200 PETALING JAYA, SELANGOR,  
Tel. +60 3 750 5214, Fax. +60 3 757 4880

**Mexico:** 5900 Gateway East, Suite 200, EL PASO, TEXAS 79905,  
Tel. +9-5 800 234 7381

**Middle East:** see Italy

**Netherlands:** Postbus 90050, 5600 PB EINDHOVEN, Bldg. VB,  
Tel. +31 40 27 82785, Fax. +31 40 27 88399

**New Zealand:** 2 Wagener Place, C.P.O. Box 1041, AUCKLAND,  
Tel. +64 9 849 4160, Fax. +64 9 849 7811

**Norway:** Box 1, Manglerud 0612, OSLO,  
Tel. +47 22 74 8000, Fax. +47 22 74 8341

**Philippines:** Philips Semiconductors Philippines Inc.,  
106 Valero St. Salcedo Village, P.O. Box 2108 MCC, MAKATI,  
Metro MANILA, Tel. +63 2 816 6380, Fax. +63 2 817 3474

**Poland:** Ul. Lukiska 10, PL 04-123 WARSZAWA,  
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**Portugal:** see Spain

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**Russia:** Philips Russia, Ul. Usatcheva 35A, 119048 MOSCOW,  
Tel. +7 095 755 6918, Fax. +7 095 755 6919

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Tel. +65 350 2538, Fax. +65 251 6500

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2092 JOHANNESBURG, P.O. Box 7430 Johannesburg 2000,  
Tel. +27 11 470 5911, Fax. +27 11 470 5494

**South America:** Rua do Rocio 220, 5th floor, Suite 51,  
04552-903 São Paulo, SÃO PAULO - SP, Brazil,  
Tel. +55 11 821 2333, Fax. +55 11 829 1849

**Spain:** Balmes 22, 08007 BARCELONA,  
Tel. +34 3 301 6312, Fax. +34 3 301 4107

**Sweden:** Kottbygatan 7, Akalla, S-16485 STOCKHOLM,  
Tel. +46 8 632 2000, Fax. +46 8 632 2745

**Switzerland:** Allmendstrasse 140, CH-8027 ZÜRICH,  
Tel. +41 1 488 2686, Fax. +41 1 481 7730

**Taiwan:** Philips Semiconductors, 6F, No. 96, Chien Kuo N. Rd., Sec. 1,  
TAIPEI, Taiwan Tel. +886 2 2134 2870, Fax. +886 2 2134 2874

**Thailand:** PHILIPS ELECTRONICS (THAILAND) Ltd.,  
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Tel. +66 2 745 4090, Fax. +66 2 398 0793

**Turkey:** Talatpasa Cad. No. 5, 80640 GÜLTEPE/ISTANBUL,  
Tel. +90 212 279 2770, Fax. +90 212 282 6707

**Ukraine:** PHILIPS UKRAINE, 4 Patrice Lumumba str., Building B, Floor 7,  
252042 KIEV, Tel. +380 44 264 2776, Fax. +380 44 268 0461

**United Kingdom:** Philips Semiconductors Ltd., 276 Bath Road, Hayes,  
MIDDLESEX UB3 5BX, Tel. +44 181 730 5000, Fax. +44 181 754 8421

**United States:** 811 East Arques Avenue, SUNNYVALE, CA 94088-3409,  
Tel. +1 800 234 7381

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**Yugoslavia:** PHILIPS, Trg N. Pasica 5/v, 11000 BEOGRAD,  
Tel. +381 11 625 344, Fax. +381 11 635 777

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